

# Jing Zhang

## List of Publications by Year in descending order

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28  
papers

1,130  
citations

623574

14  
h-index

610775

24  
g-index

28  
all docs

28  
docs citations

28  
times ranked

1063  
citing authors

#	ARTICLE	IF	CITATIONS
1	Analysis of Internal Quantum Efficiency and Current Injection Efficiency in III-Nitride Light-Emitting Diodes. <i>Journal of Display Technology</i> , 2013, 9, 212-225.	1.3	181
2	Improvement in spontaneous emission rates for InGaN quantum wells on ternary InGaN substrate for light-emitting diodes. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	164
3	Effect of crystal-field split-off hole and heavy-hole bands crossover on gain characteristics of high Al-content AlGaIn quantum well lasers. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	135
4	Large optical gain AlGaIn-delta-GaN quantum wells laser active regions in mid- and deep-ultraviolet spectral regimes. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	120
5	Optical Gain and Laser Characteristics of InGaIn Quantum Wells on Ternary InGaIn Substrates. <i>IEEE Photonics Journal</i> , 2013, 5, 2600111-2600111.	1.0	100
6	FDTD Analysis on Extraction Efficiency of GaN Light-Emitting Diodes With Microsphere Arrays. <i>Journal of Display Technology</i> , 2013, 9, 317-323.	1.3	97
7	234-nm and 246-nm AlIn-Delta-GaN quantum well deep ultraviolet light-emitting diodes. <i>Applied Physics Letters</i> , 2018, 112, .	1.5	55
8	Light Extraction Efficiency Analysis of Flip-Chip Ultraviolet Light-Emitting Diodes With Patterned Sapphire Substrate. <i>IEEE Photonics Journal</i> , 2018, 10, 1-13.	1.0	46
9	Physics and polarization characteristics of 298-nm AlIn-delta-GaN quantum well ultraviolet light-emitting diodes. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	44
10	Analysis of Polarization-Dependent Light Extraction and Effect of Passivation Layer for 230-nm AlGaIn Nanowire Light-Emitting Diodes. <i>IEEE Photonics Journal</i> , 2017, 9, 1-12.	1.0	35
11	Monolithic Integration of GaN Nanowire Light-Emitting Diode With Field Effect Transistor. <i>IEEE Electron Device Letters</i> , 2019, 40, 427-430.	2.2	33
12	Effect of KOH passivation for top-down fabricated InGaIn nanowire light emitting diodes. <i>Journal of Applied Physics</i> , 2019, 126, .	1.1	31
13	Proposal and physics of AlInN-delta-GaN quantum well ultraviolet lasers. <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	20
14	Design analysis of phosphor-free monolithic white light-emitting-diodes with InGaIn/ InGaIn multiple quantum wells on ternary InGaIn substrates. <i>AIP Advances</i> , 2015, 5, .	0.6	17
15	AlGaIn-Delta-GaN Quantum Well for DUV LEDs. <i>Photonics</i> , 2020, 7, 87.	0.9	11
16	Influence of quantum well design on light polarization switching in AlGaIn ultraviolet emitters. <i>AIP Advances</i> , 2018, 8, 085125.	0.6	7
17	Analysis of InGaIn-Delta-InN Quantum Wells on InGaIn Substrates for Red Light Emitting Diodes and Lasers. <i>IEEE Photonics Journal</i> , 2021, 13, 1-10.	1.0	7
18	Realization of electrically driven AlGaIn micropillar array deep-ultraviolet light emitting diodes at 286 nm. <i>AIP Advances</i> , 2021, 11, 095005.	0.6	6

#	ARTICLE	IF	CITATIONS
19	Proposal and Realization of Vertical GaN Nanowire Static Induction Transistor. IEEE Electron Device Letters, 2019, 40, 259-262.	2.2	5
20	AlGaIn nanowires with inverse taper for flexible DUV emitters. JPhys Photonics, 2021, 3, 024016.	2.2	5
21	Physics of high-efficiency 240-260nm deep-ultraviolet lasers and light-emitting diodes on AlGaIn substrate. Journal of Applied Physics, 2020, 127, .	1.1	4
22	450 nm Gallium Nitride Alternating Current Light-Emitting Diode. IEEE Photonics Journal, 2020, 12, 1-6.	1.0	3
23	Ultraviolet Electrostatic Field Effect Light-Emitting Diode. IEEE Photonics Journal, 2020, 12, 1-8.	1.0	1
24	Electrostatic Field Effect Light-Emitting Diode. IEEE Photonics Journal, 2020, 12, 1-8.	1.0	1
25	Demonstration of Flexible DUV Light Emitting Diodes through Formation of Nanowires with Inverse-Taper. , 2021, , .		1
26	Narrow Linewidth Photoluminescence from Top-Down Fabricated 20 nm InGaIn/GaN Quantum Dots at Room Temperature. , 2020, , .		1
27	Analysis of AlGaIn substrate for high-efficiency 240-260nm deep-UV lasers. , 2019, , .		0
28	Analysis on light extraction property of AlGaIn-based flip-chip ultraviolet light-emitting diodes by the use of self-assembled SiO <sub>2</sub> microsphere array. , 2019, , .		0